Electronic Supplementary Information (ESI)

Tunable Dielectric Constant of Polyimide-Barium Titanate Nanocomposite Materials as the Gate Dielectrics for Organic Thin Film Transistors Applications

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Fig. S1. FTIR spectra of BT ceramic.



Fig. S2. SEM micrograph of dielectric surface: (a) PI-BT0, (b) PI-BT2, (c) PI-BT5, (d) PI-

BT8, (e) PI-BT10, and (f) PI-BT12.



Fig. S3. (a) TGA and (b) DSC curves of PI-BTX hybrid materials.







Fig. S4. Output characteristics of the OTFTs based on (a) PI-BT0, (b) PI-BT2, (c) PI-BT5,

(d) PI-BT8, (e) PI-BT10, and (f) PI-BT12 hybrid dielectric.



Fig. S5. Water contact angles on (a) PI-BT0, (b) PI-BT2, (c) PI-BT5, (d) PI-BT8, (e) PI-

BT10 and (f) PB12 hybrid surface.



Fig. S6. Diiodomethane contact angles on (a) PI-BT0, (b) PI-BT2, (c) PI-BT5, (d) PI-BT8,

(e) **PI-BT10** and (f) **PI-BT12** hybrid surface.



Fig. S7. SEM images of pentacene deposited on dielectric films: (a) PI-BT0, (b) PI-BT2, (c)

PI-BT5, (d) PI-BT8, (e) PI-BT10 and (f) PI-BT12